

Supporting Information

Fuctionalized Anthradithiophenes for Organic Field-Effect Transistors

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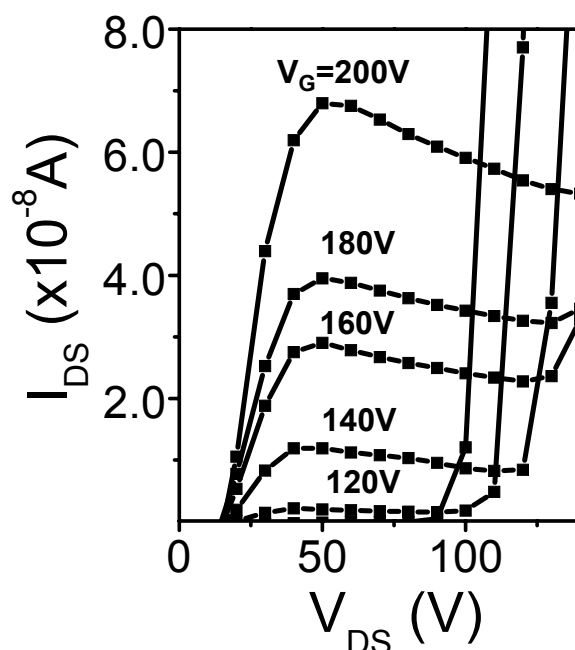


Figure 1. Output characteristics of 50 nm thick DFPADT FET as an n-channel semiconductor. Films were fabricated on HMDS-treated SiO₂ at 150 °C.

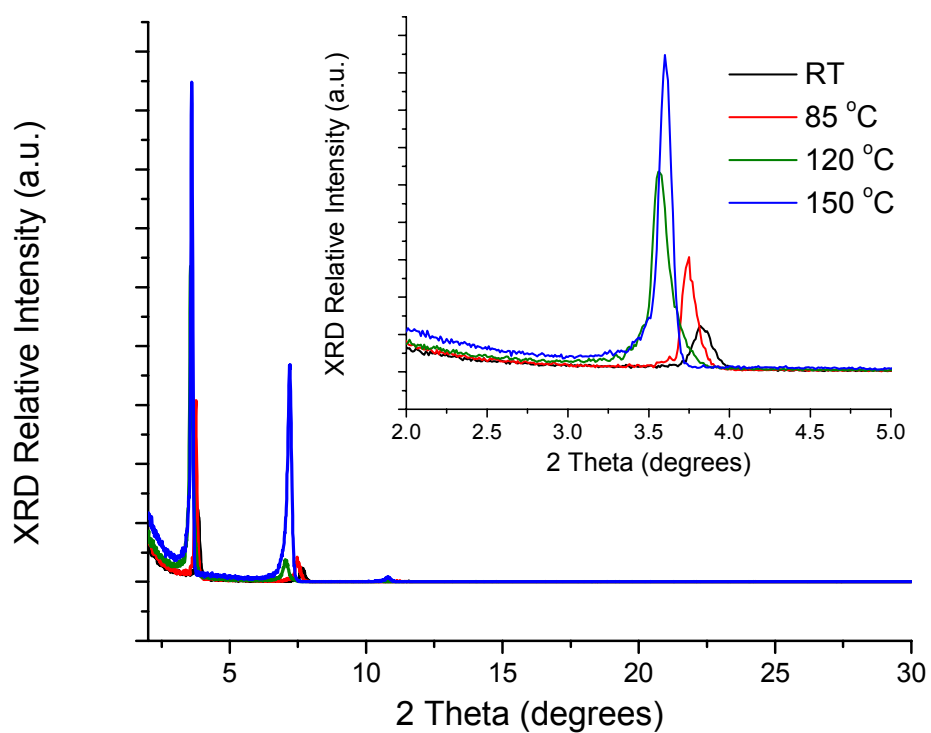


Figure 2. XRD pattern of 50 nm thick DFPADT films grown on HMDS-treated substrates at various substrate temperature (RT, 85, 120, and 150 °C).